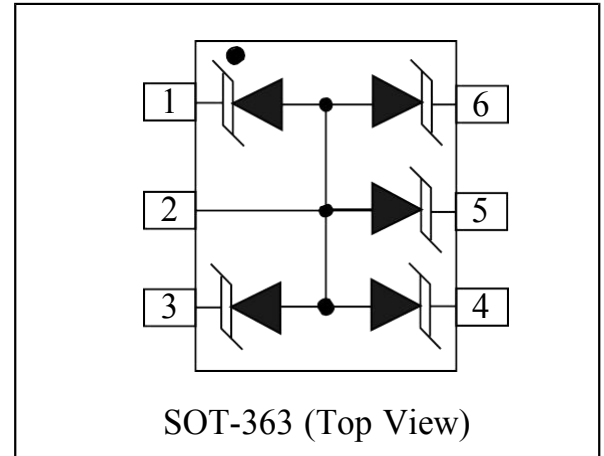


Features

80Watts peak pulse power ($t_p = 8/20\mu s$)
 Tiny SOT363 package
 Solid-state silicon-avalanche technology
 Low clamping voltage
 Low leakage current
 Protection five data/power line
 IEC 61000-4-2 $\pm 30kV$ contact $\pm 30kV$ air
 IEC 61000-4-4 (EFT) 40A (5/50ns)
 IEC 61000-4-5 (Lightning) 8 A (8/20 μs)

Schematic & PIN Configuration



Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{PP}	80	Watts
Peak Pulse Current ($t_p = 8/20\mu s$) (note1)	I_{pp}	8	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	30 30	kV
Lead Soldering Temperature	T_L	260(10seconds)	°C
Junction Temperature	T_J	-55 to + 125	°C
Storage Temperature	T_{stg}	-55 to + 125	°C

Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	6.0			V
Reverse Leakage Current	I_R	$V_{RWM}=5V, T=25^{\circ}C$		50	500	nA
Clamping Voltage	V_C	$I_{PP}=8A, t_p=8/20\mu s$		12		V
Junction Capacitance	C_j	$V_R = 0V, f = 1MHz$ IO to IO		30		pF
		$V_R = 0V, f = 1MHz$ IO to GND		70		

Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)

Figure 1: Peak Pulse Power vs. Pulse Time

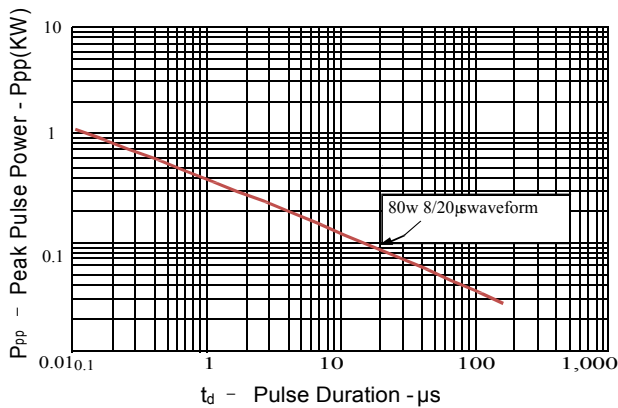


Figure 2: Power Derating Curve

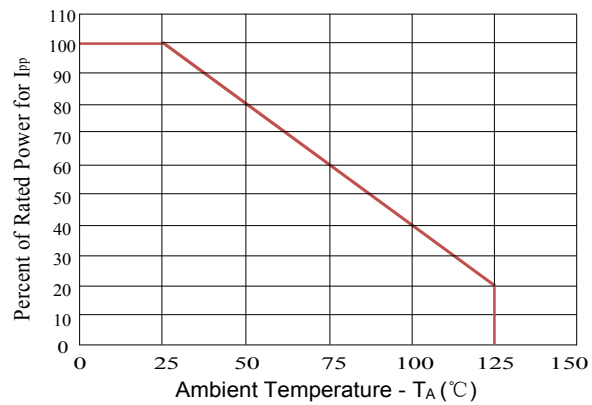


Figure3: Pulse Waveform

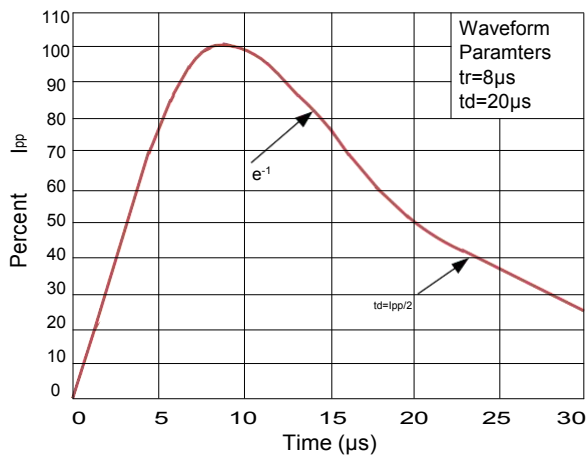
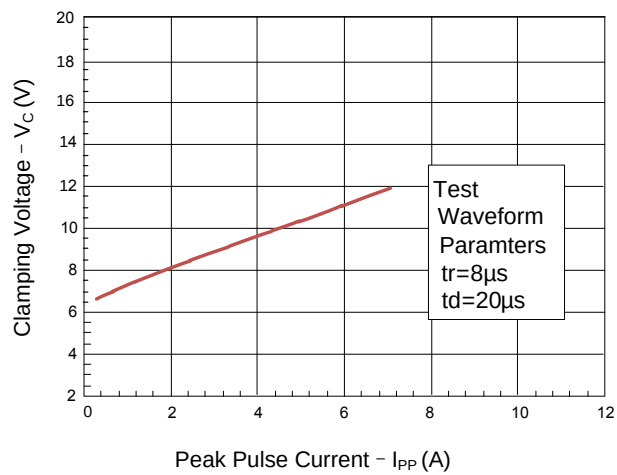


Figure 4: Clamping Voltage vs. I_{pp}



Outline Drawing – SOT363

